

## Product Overview

### FGA6065ADF: IGBT, 650 V, 60 A Field Stop Trench

For complete documentation, see the data sheet.

This ADF IGBT series adopted Field Stop Trench 3rd generation IGBT which offer extreme low  $R_{ds(on)}$  and much faster switching characteristics for outstanding efficiency. And this kind of technology is fully optimized to variety PFC (Power Factor Correction) topology ; Single boost, Multi channel interleaved etc with over 20KHz switching performance. TO3P package provide Super Low thermal resistance for much wider SOA for system stability.

### Features

- Maximum Junction Temperature :  $T_J = 175\text{ }^\circ\text{C}$
- Positive Temperature Co-efficient for Easy Parallel Operating
- High Current Capability
- Low Saturation Voltage:  $V_{CE(sat)} = 1.8\text{ V (Typ.) @ } I_C = 60\text{ A}$
- 100% of the Parts Tested for  $I_{LM} (1)$
- High Input Impedance
- Fast Switching
- RoHS Compliant

### Part Electrical Specifications

Product	Compliance	Status	$V_{ES}^{(BR)C}$ Typ (V)	$I_C$ Max (A)	$V_{CE(sat)}$ Typ (V)	$V_F$ Typ (V)	$E_{off}$ Typ (mJ)	$E_{on}$ Typ (mJ)	$T_{rr}$ Typ (ns)	$I_T$ Typ (A)	Gate Charge Typ (nC)	Short Circuit Withstand ( $\mu$ s)	$E_{AS}$ Typ (mJ)	$P_D$ Max (W)	Co- Pack aged Diode	Pack age Type
FGA6065ADF	Pb-free Halide free	Active	650	60	1.8	1.8	0.52	2.46	271	-	84	-	-	306	No	TO-3P-3L

For more information please contact your local sales support at [www.onsemi.com](http://www.onsemi.com).

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